

Ordering number : ENN7080

P-Channel Silicon MOSFET



# MCH6307

## Ultrahigh-Speed Switching Applications

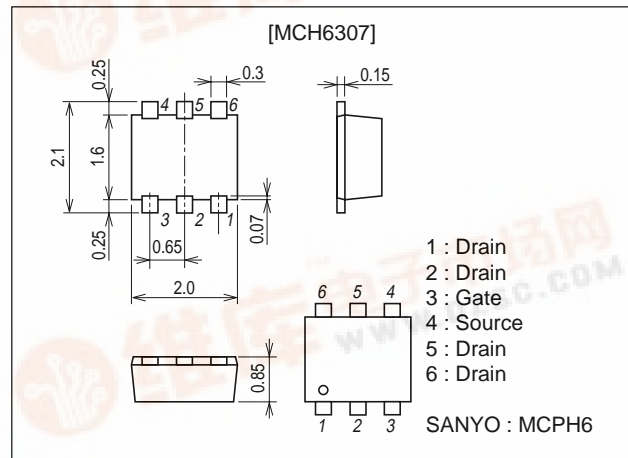
### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 1.8V drive.

### Package Dimensions

unit : mm

2193A



### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-12	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±8	V
Drain Current (DC)	I <sub>D</sub>		-5	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-20	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm)	1.5	W
		Mounted on an FR4 board, PW≤3s	2.0	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0	-12			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-12V, V <sub>GS</sub> =0			-10	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±6.4V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-6V, I <sub>D</sub> =-1mA	-0.3		-1.0	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-6V, I <sub>D</sub> =-3A	5.8	8.5		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-3A, V <sub>GS</sub> =-4.5V		35	46	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-2.5V		47	66	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-0.3A, V <sub>GS</sub> =-1.8V		68	98	mΩ

Marking : JG

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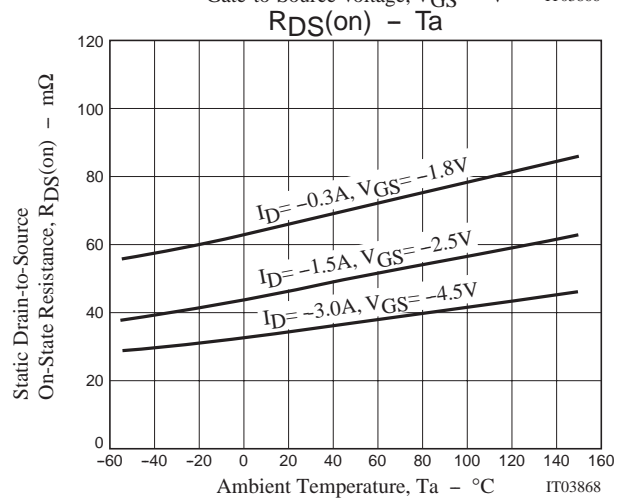
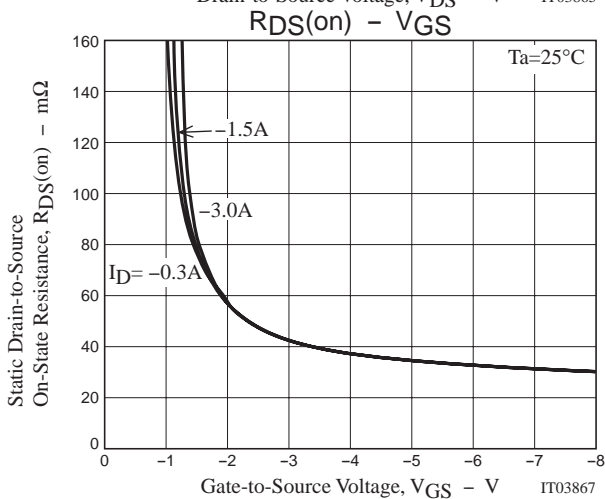
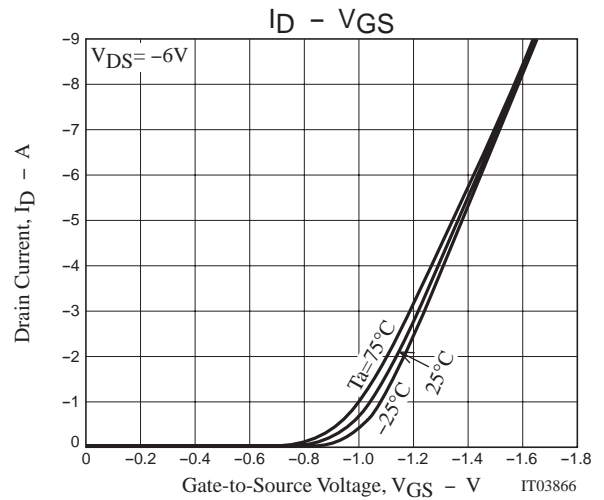
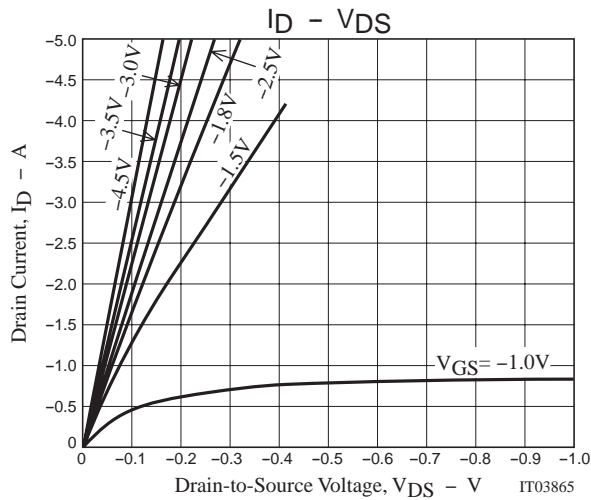
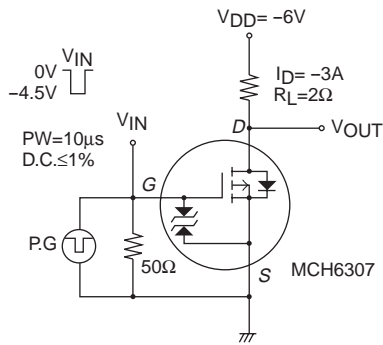


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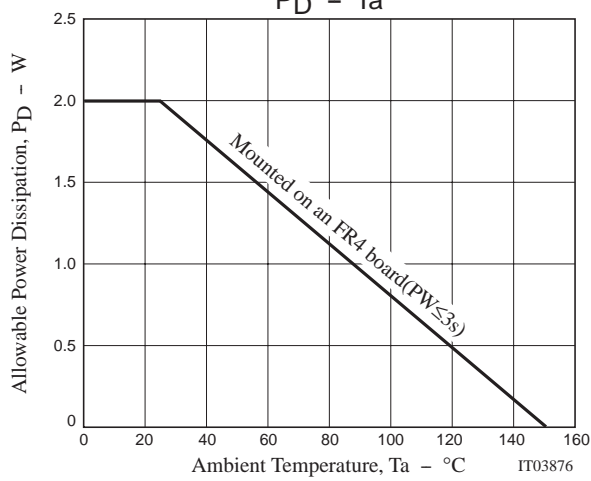
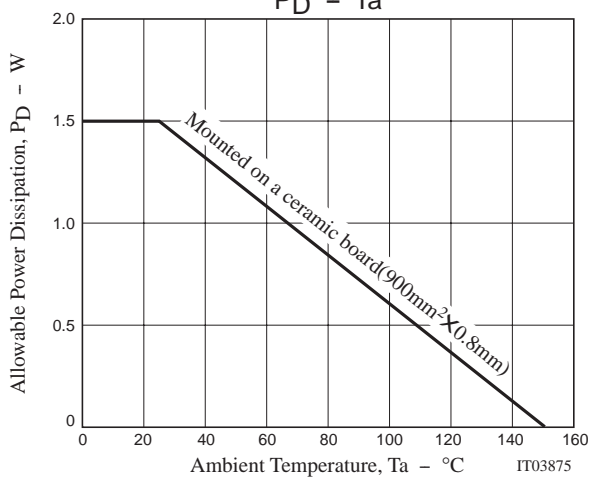
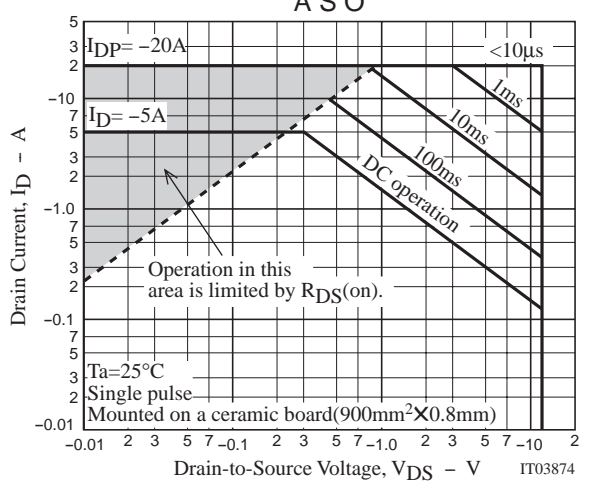
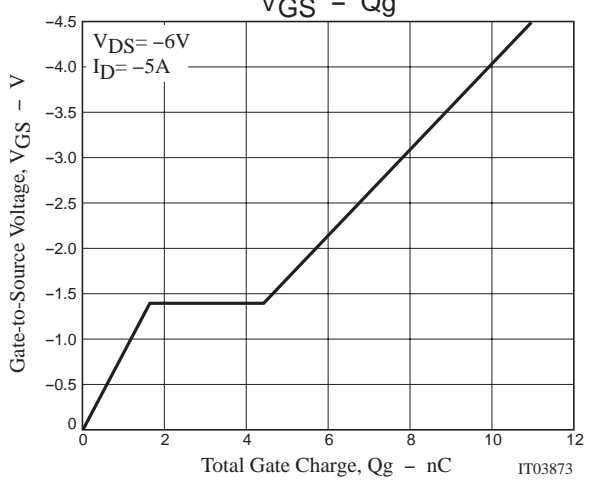
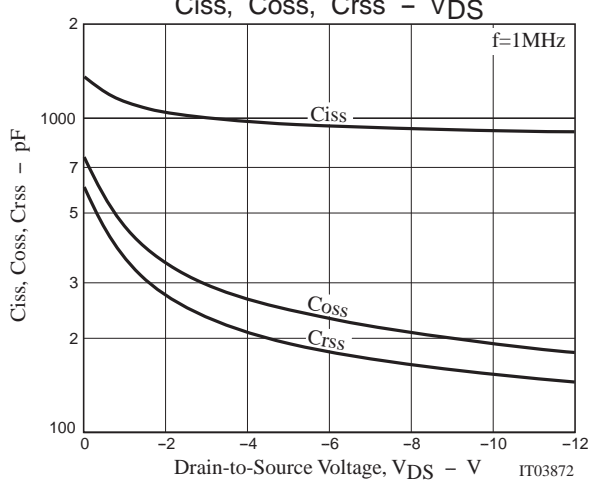
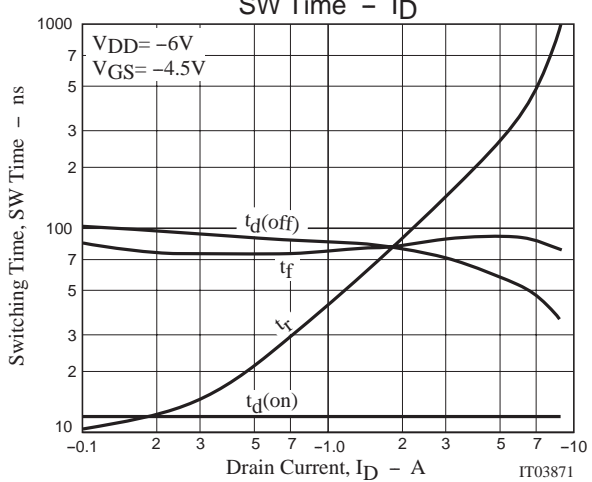
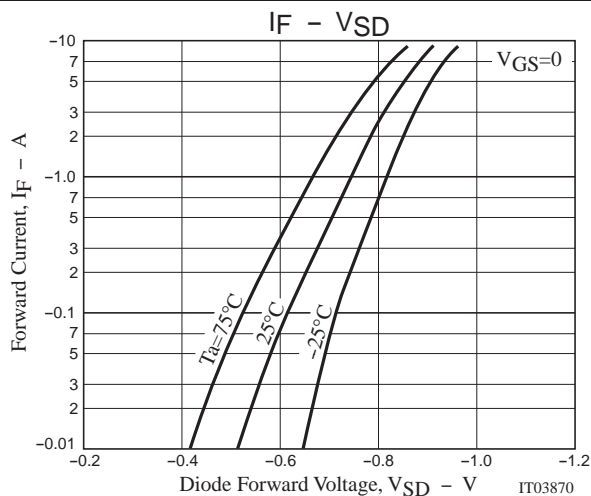
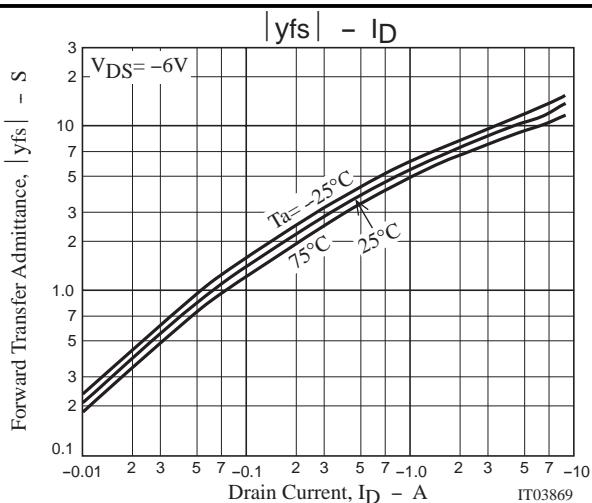
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	$V_{DS}=-6V, f=1MHz$		940		pF
Output Capacitance	Coss	$V_{DS}=-6V, f=1MHz$		230		pF
Reverse Transfer Capacitance	Crss	$V_{DS}=-6V, f=1MHz$		180		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		12		ns
Rise Time	$t_r$	See specified Test Circuit.		143		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		71		ns
Fall Time	$t_f$	See specified Test Circuit.		89		ns
Total Gate Charge	Qg	$V_{DS}=-6V, V_{GS}=-4.5V, I_D=-5A$		11		nC
Gate-to-Source Charge	Qgs	$V_{DS}=-6V, V_{GS}=-4.5V, I_D=-5A$		1.6		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=-6V, V_{GS}=-4.5V, I_D=-5A$		2.8		nC
Diode Forward Voltage	$V_{SD}$	$I_S=-5A, V_{GS}=0$		-0.85	-1.5	V

## Switching Time Test Circuit



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